

ABSTRACT OF THE DISCLOSURE

A hermetically coated device includes an integrated semiconductor circuit die, a first layer comprising an inorganic material, the first layer enveloping the integrated semiconductor circuit die, a second layer, the second layer enveloping the integrated semiconductor circuit die. Formation of such device includes steps of providing an integrated semiconductor circuit die, applying a first layer comprising an inorganic material, the first layer enveloping the integrated semiconductor circuit die, and applying a second layer, the second layer enveloping the integrated semiconductor circuit die.

20250906 092302